

Features

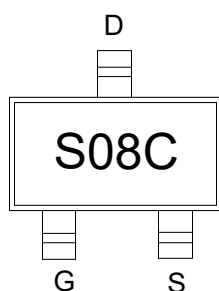
- Trench Power LV MOSFET technology
- High Density Cell Design for Low $R_{DS(ON)}$
- High Speed switching

Application

- CoBattery protection
- Load switch
- Power management

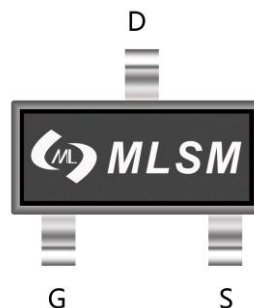
Product Summary

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
60V	144mΩ@10V	2.6A
	200mΩ@4.5V	

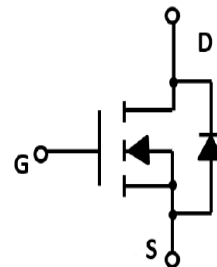


S08C: Device code

Marking and pin assignment



SOT-23 top view



Schematic diagram



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
--------	-----------	--------	------

Common Ratings (TC=25°C Unless Otherwise Noted)

V_{DS}	Drain-Source Breakdown Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
I_S	Diode Continuous Forward Current	$T_C=25^{\circ}C$	1.3
			A

Mounted on Large Heat Sink

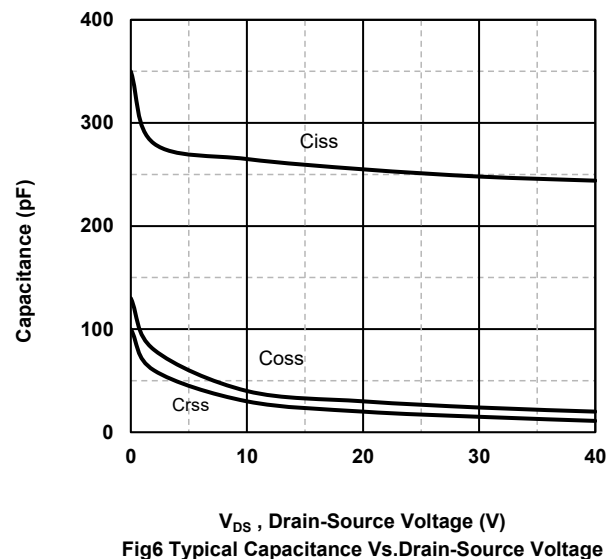
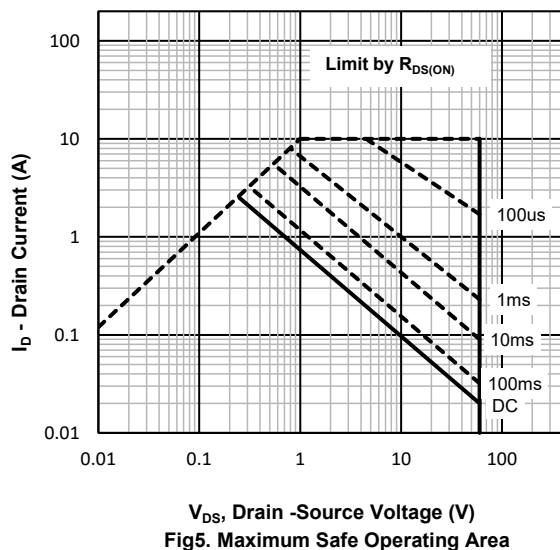
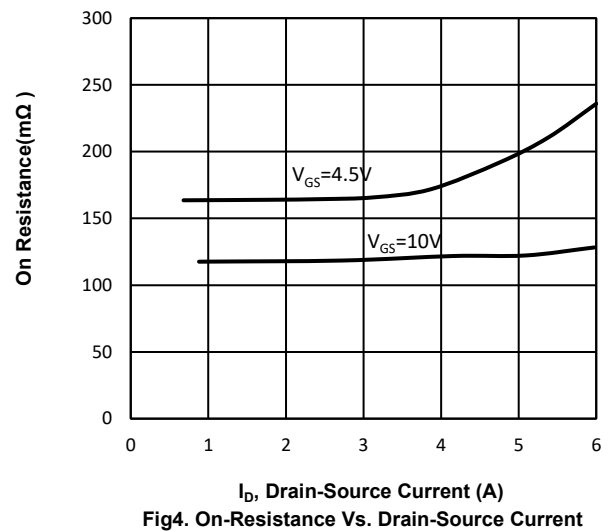
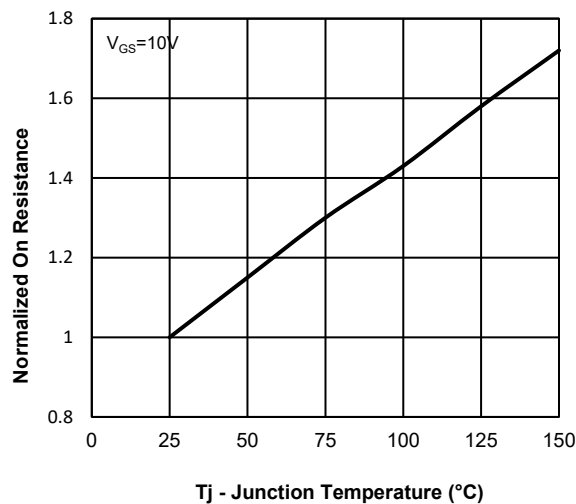
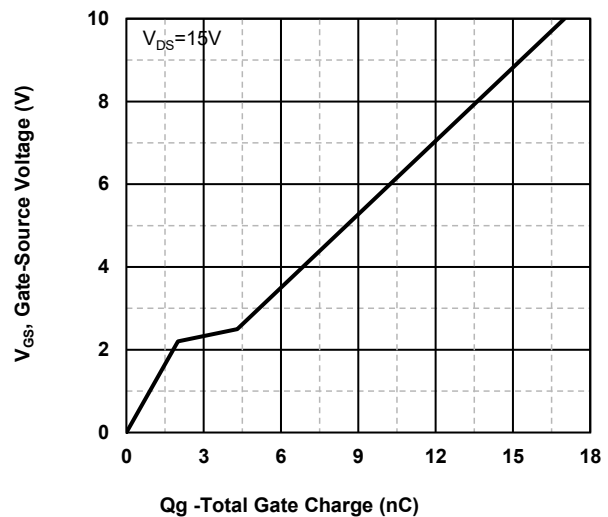
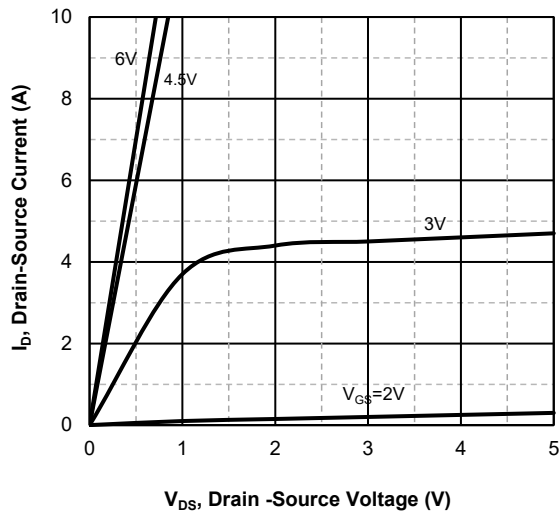
I_{DM}	Pulse Drain Current Tested	$T_C=25^{\circ}C$	6	A
I_D	Continuous Drain Current	$T_C=25^{\circ}C$	2.6	A
P_D	Maximum Power Dissipation	$T_C=25^{\circ}C$	1.6	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		115	°C/W

Ordering Information (Example)

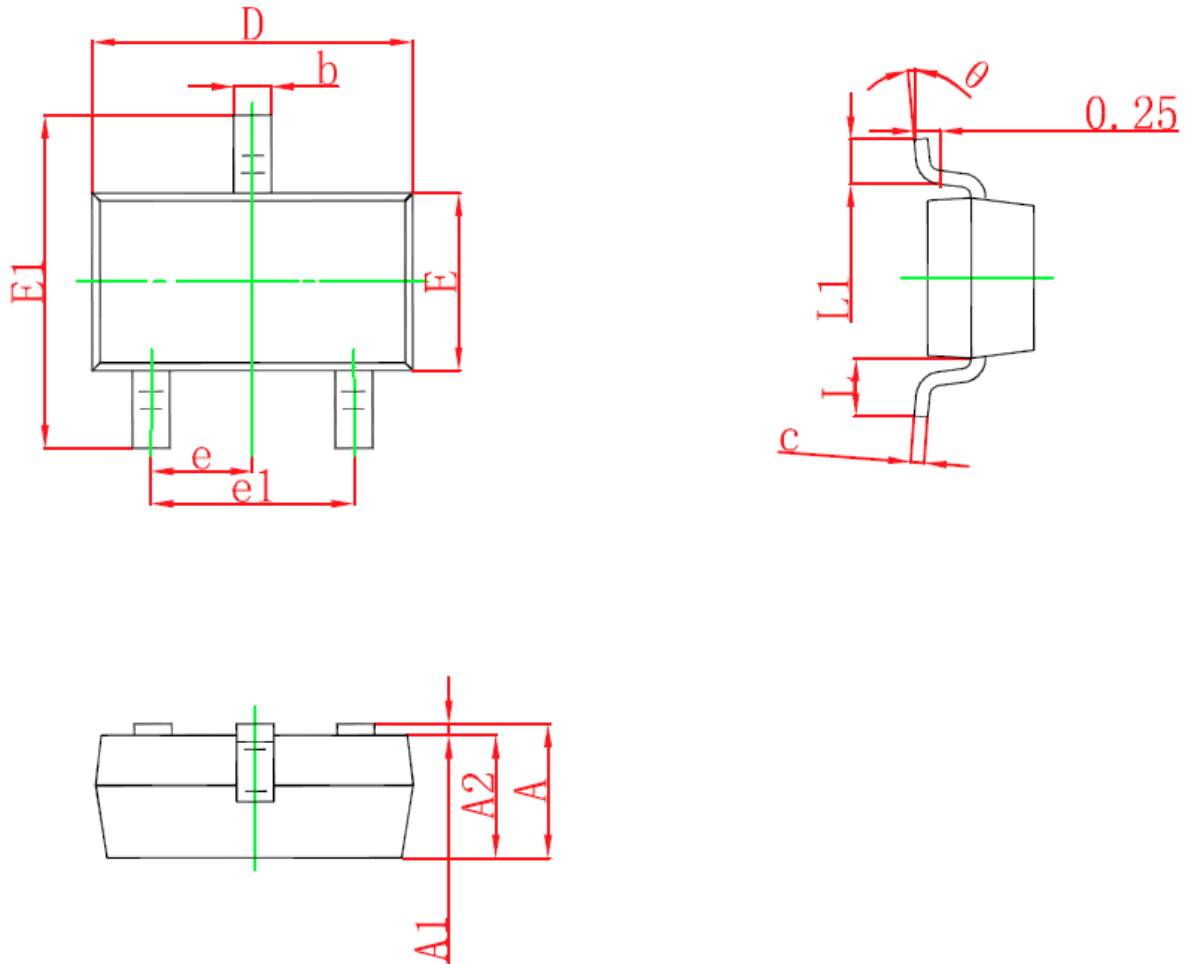
Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
Si2308CDS	SOT-23	S08C	3,000	45,000	180,000	7"reel

Electrical Characteristics (T _J =25℃ unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T _J = 25℃ (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	60	–	–	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} =0V	–	–	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	–	–	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	–	3.0	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =1.9A	–	120	144	mΩ
		V _{GS} =4.5V, I _D =1.5A	–	160	200	mΩ
Dynamic Electrical Characteristics @ T _J = 25℃ (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =30V, V _{GS} =0V, f=1MHz	–	105	–	pF
C _{OSS}	Output Capacitance		–	55	–	pF
C _{RSS}	Reverse Transfer Capacitance		–	7	–	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =30V, I _D =1.9A, V _{GS} =4.5V	–	1.05	–	nC
Q _{gs}	Gate Source Charge		–	0.62	–	nC
Q _{gd}	Gate Drain Charge		–	0.17	–	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =30V, R _L =20Ω, I _D =1.5A, V _{GS} =10V, R _G =1Ω	–	8	–	nS
t _r	Turn-on Rise Time		–	5	–	nS
t _{d(off)}	Turn-Off Delay Time		–	11	–	nS
t _f	Turn-Off Fall Time		–	3	–	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25℃, I _S =1.5A	–	0.85	1.2	V

Typical Operating Characteristics



SOT-23 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E1	2.250	2.550	0.088	0.100
E	1.200	1.400	0.047	0.055
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°